

TSM9434

20V P-Channel MOSFET



SOP-8

Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gat
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-20	40 @ V _{GS} = -4.5V	-6.4	
	60 @ V _{GS} = -2.5V	-5.1	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

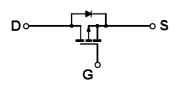
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM9434CS RL	SOP-8	T&R

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current		I _D	-6.4	А	
Pulsed Drain Current		I _{DM} ±10		А	
Continuous Source Current (Diode C	Conduction) ^{a,b}	I _S	-2.5	А	
Mariana Dama Dissipation	Ta = 25 °C		2.5	W	
Maximum Power Dissipation	Ta = 70 °C	P _D	1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Tem	nperature Range	T _J , T _{STG} - 55 to +150		°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	50	°C/W

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

TSM9434

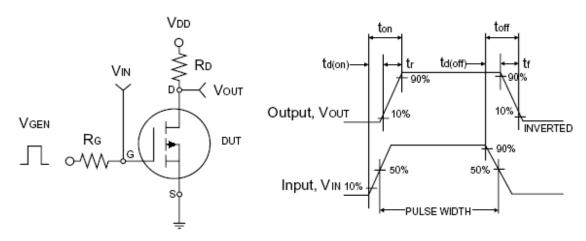
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Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250uA$	$V_{GS(TH)}$	-0.4		-1.0	V
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}	1		-1.0	uA
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
On-State Drain Current	V _{DS} ≤-5V, V _{GS} = -4.5V	$I_{D(ON)}$	-10			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_D = -6.4A$	J	1	31	40	mΩ
Dialii-Source Off-State Resistance	$V_{GS} = -2.5V$, $I_D = -5.1A$	R _{DS(ON)}		45	60	
Forward Transconductance	$V_{DS} = -9V, I_D = -6.4A$	g fs	1	14		S
Diode Forward Voltage	$I_S = -2.5A$, $V_{GS} = 0V$	V_{SD}	1	- 0.9	-1.2	V
Dynamic ^b				•		
Total Gate Charge	$V_{DS} = -10V$, $I_D = -6.4A$,	Q_g		12.5	19	
Gate-Source Charge	$V_{DS} = -10V, I_D = -0.4A,$ $V_{GS} = -4.5V$	Q_gs		1.7		nC
Gate-Drain Charge	V _{GS} = -4.5 V	Q_gd		3.3		
Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$	C_{iss}		1020		
Output Capacitance	$v_{DS} = -10V, v_{GS} = 0V,$ f = 1.0MHz	C_{oss}		191		pF
Reverse Transfer Capacitance	1 - 1.0IVII IZ	C_{rss}	-	140		
Switching ^c						
Turn-On Delay Time	V = 40V D = 400	$t_{d(on)}$	-	25	40	
Turn-On Rise Time	$V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V.$	t _r	-	43	65	nS
Turn-Off Delay Time	$R_{G} = 6\Omega$	$t_{d(off)}$	-	71	110	113
Turn-Off Fall Time	17G - 022	t _f		48	75	

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



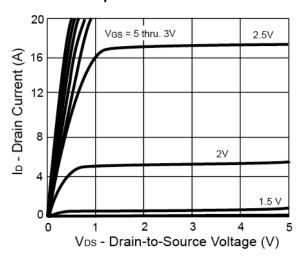




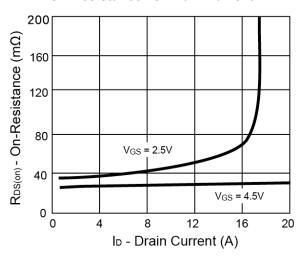


Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

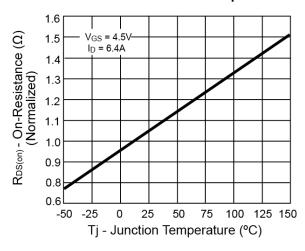
Output Characteristics



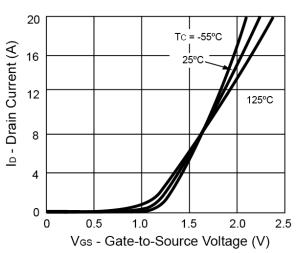
On-Resistance vs. Drain Current



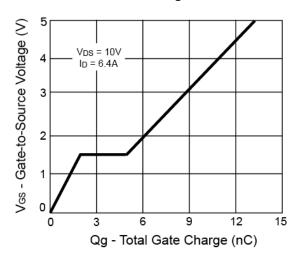
On-Resistance vs. Junction Temperature



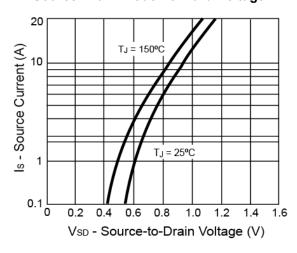
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





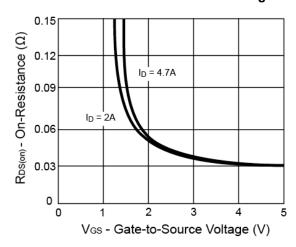




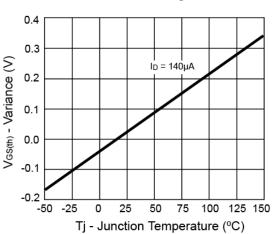


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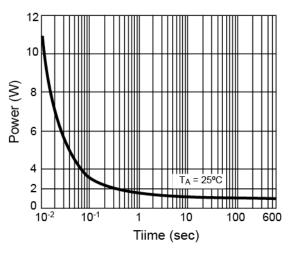
On-Resistance vs. Gate-Source Voltage



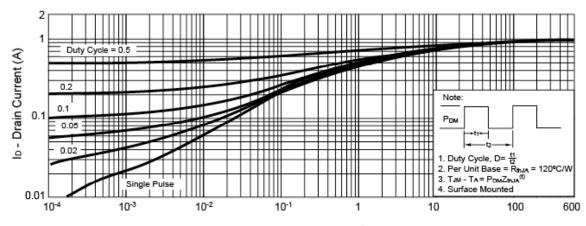
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



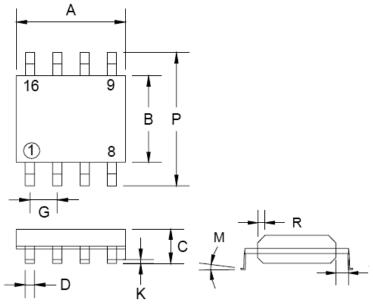
Square Wave Pulse Duration (sec)







SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



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